SLOVENSKI STANDARD

oSIST prEN IEC 63550-3:2025

01-november-2025

Polprevodniški elementi - Nevromorfne naprave - 3. del: Metoda ocenjevanja od konic odvisne plastičnosti v memristorskih napravah

Semiconductor devices - Neuromorphic devices - Part 3: Evaluation method of spike dependent plasticity in memristor devices

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Dispositifs à semiconducteurs - Dispositifs neuromorphiques - Partie 3: Méthode d'évaluation de la plasticité dépendant de la temporisation des impulsions pré- Et postsynaptiques dans les dispositifs à memristance

Ta slovenski standard je istoveten z: **prEN IEC 63550-3:2025**

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ICS:

31.080.99	Drugi polprevodniški elementi	Other semiconductor devices

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47/2941/CDV

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SECRETARIAT: Korea, Republic of	SECRETARY: Mr Cheolung Cha
OF INTEREST TO THE FOLLOWING COMMITTEES:	HORIZONTAL FUNCTION(S):
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TITLE:

Semiconductor devices - Neuromorphic devices - Part 3: Evaluation method of spike dependent plasticity in memristor devices

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